

ZXMC4559DN8

COMPLEMENTARY 60V ENHANCEMENT MODE MOSFET

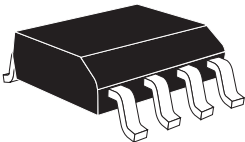
SUMMARY

N-Channel $V_{(BR)DSS} = 60V$; $R_{DS(ON)} = 0.055\Omega$; $I_D = 4.7A$

P-Channel $V_{(BR)DSS} = -60V$; $R_{DS(ON)} = 0.105\Omega$; $I_D = -3.9A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



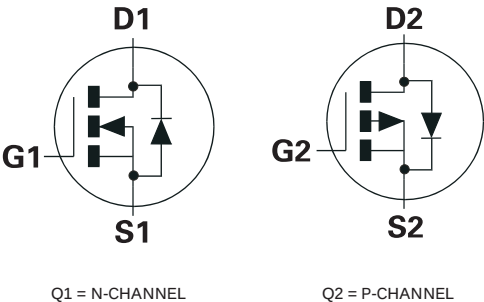
SO8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- Motor Drive
- LCD backlighting



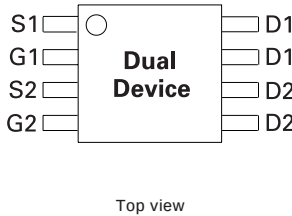
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXMC4559DN8TA	7"	12mm	500 units
ZXMC4559DN8TC	13"	12mm	2500 units

DEVICE MARKING

- ZXMC
4559

PINOUT



ZXMC4559DN8

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	N-Channel	P-Channel	UNIT
Drain-Source Voltage	V_{DSS}	60	-60	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current @ $V_{GS}=10V$; $T_A=25^\circ C$ (b) (d) @ $V_{GS}=10V$; $T_A=25^\circ C$ (b) (d) @ $V_{GS}=10V$; $T_A=25^\circ C$ (a) (d)	I_D	4.7	-3.9	A
		3.7	-2.8	A
		3.6	-2.6	A
Pulsed Drain Current (c)	I_{DM}	22.2	-18.3	A
Continuous Source Current (Body Diode) (b)	I_S	3.4	-3.2	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	22.2	-18.3	A
Power Dissipation at $T_A=25^\circ C$ (a) (d)	P_D	1.25		W
Linear Derating Factor		10		mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a) (e)	P_D	1.8		W
Linear Derating Factor		14		mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) (d)	P_D	2.1		W
Linear Derating Factor		17		mW/ $^\circ C$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ C$

THERMAL RESISTANCE

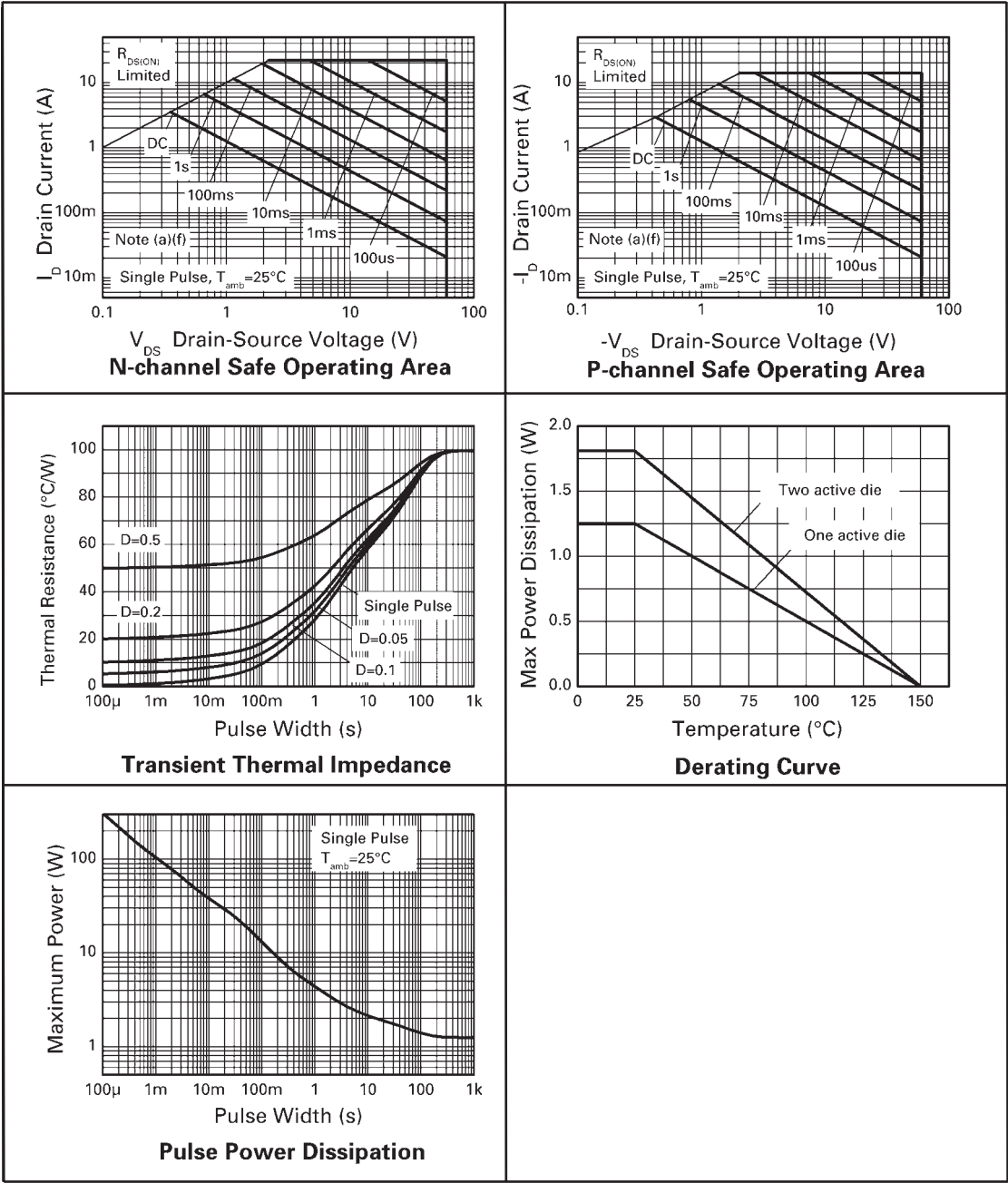
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a) (d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (b) (e)	$R_{\theta JA}$	69	$^\circ C/W$
Junction to Ambient (b) (d)	$R_{\theta JA}$	58	$^\circ C/W$

Notes

- (a) For a dual device surface mounted on 25mm x 25mm FR4 PCB with coverage of single sided 1oz copper in still air conditions.
(b) For a dual device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
(c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.02$ pulse width=300 μs - pulse width limited by maximum junction temperature.
(d) For a device with one active die.
(e) For device with 2 active die running at equal power.

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CHARACTERISTICS



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N-CHANNEL

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	60			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μA	V _{DS} =60V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1.0			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}			0.055	Ω	V _{GS} =10V, I _D =4.5A
				0.075	Ω	V _{GS} =4.5V, I _D =4.0A
Forward Transconductance ^{(1) (3)}	g _{fs}		10.2		S	V _{DS} =15V, I _D =4.5A
DYNAMIC ⁽³⁾						
Input Capacitance	C _{iss}		1063		pF	V _{DS} =30V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		104		pF	
Reverse Transfer Capacitance	C _{rss}		64		pF	
SWITCHING ^{(2) (3)}						
Turn-On Delay Time	t _{d(on)}		3.5		ns	V _{DD} =30V, I _D =1A R _G =6.0Ω, V _{GS} =10V
Rise Time	t _r		4.1		ns	
Turn-Off Delay Time	t _{d(off)}		26.2		ns	
Fall Time	t _f		10.6		ns	
Gate Charge	Q _g		11.0		nC	V _{DS} =30V, V _{GS} =5V, I _D =4.5A
Total Gate Charge	Q _g		20.4		nC	V _{DS} =30V, V _{GS} =10V, I _D =4.5A
Gate-Source Charge	Q _{gs}		4.1		nC	
Gate-Drain Charge	Q _{gd}		5.1		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage ⁽¹⁾	V _{SD}		0.85	1.2	V	T _J =25°C, I _S =5.5A, V _{GS} =0V
Reverse Recovery Time ⁽³⁾	t _{rr}		22		ns	T _J =25°C, I _F =2.2A,
Reverse Recovery Charge ⁽³⁾	Q _{rr}		21.4		nC	di/dt= 100A/μs

NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

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P-CHANNEL

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-60			V	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			-1.0	μA	$V_{DS}=-60\text{V}$, $V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D=-250\mu\text{A}$, $V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance ⁽¹⁾	$R_{DS(on)}$			0.085 0.125	Ω Ω	$V_{GS}=-10\text{V}$, $I_D=-2.9\text{A}$ $V_{GS}=-4.5\text{V}$, $I_D=-2.4\text{A}$
Forward Transconductance ⁽¹⁾ ⁽³⁾	g_{fs}		7.2		S	$V_{DS}=-15\text{V}$, $I_D=-2.9\text{A}$
DYNAMIC ⁽³⁾						
Input Capacitance	C_{iss}		1021		pF	$V_{DS}=-30\text{ V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$
Output Capacitance	C_{oss}		83.1		pF	
Reverse Transfer Capacitance	C_{rss}		56.4		pF	
SWITCHING ⁽²⁾ ⁽³⁾						
Turn-On Delay Time	$t_{d(on)}$		3.5		ns	$V_{DD}=-30\text{V}$, $I_D=-1\text{A}$ $R_G=6.0\Omega$, $V_{GS}=-10\text{V}$
Rise Time	t_r		4.1		ns	
Turn-Off Delay Time	$t_{d(off)}$		35		ns	
Fall Time	t_f		10		ns	
Gate Charge	Q_g		12.1		nC	$V_{DS}=-30\text{V}$, $V_{GS}=-5\text{V}$, $I_D=-2.9\text{A}$
Total Gate Charge	Q_g		24.2		nC	$V_{DS}=-30\text{V}$, $V_{GS}=-10\text{V}$, $I_D=-2.9\text{A}$
Gate-Source Charge	Q_{gs}		2.5		nC	
Gate-Drain Charge	Q_{gd}		3.7		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage ⁽¹⁾	V_{SD}		-0.85	-0.95	V	$T_J=25^{\circ}\text{C}$, $I_S=-3.4\text{A}$, $V_{GS}=0\text{V}$
Reverse Recovery Time ⁽³⁾	t_{rr}		29.2		ns	$T_J=25^{\circ}\text{C}$, $I_F=-2\text{A}$, $di/dt=100\text{A}/\mu\text{s}$
Reverse Recovery Charge ⁽³⁾	Q_{rr}		39.6		nC	

NOTES

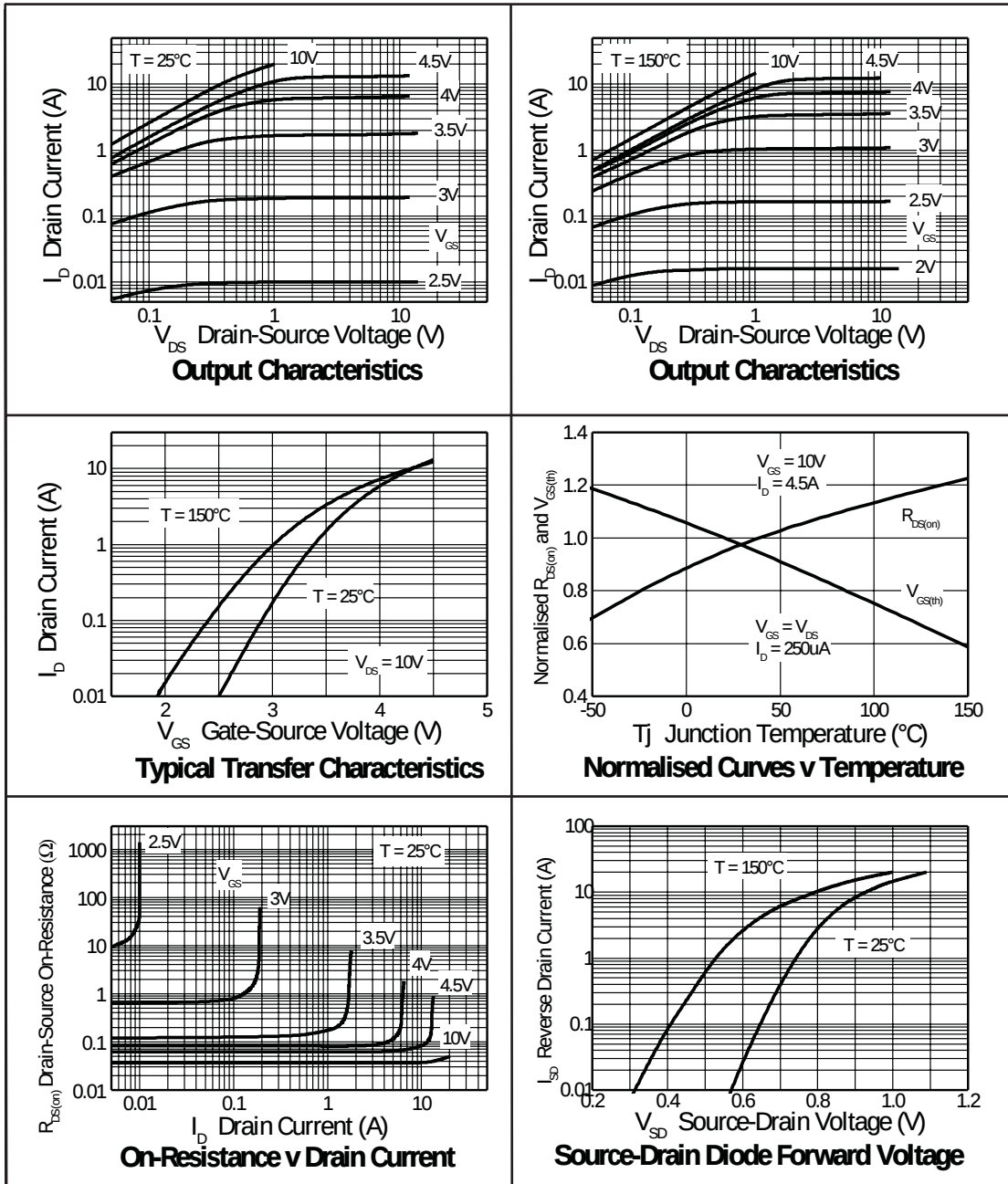
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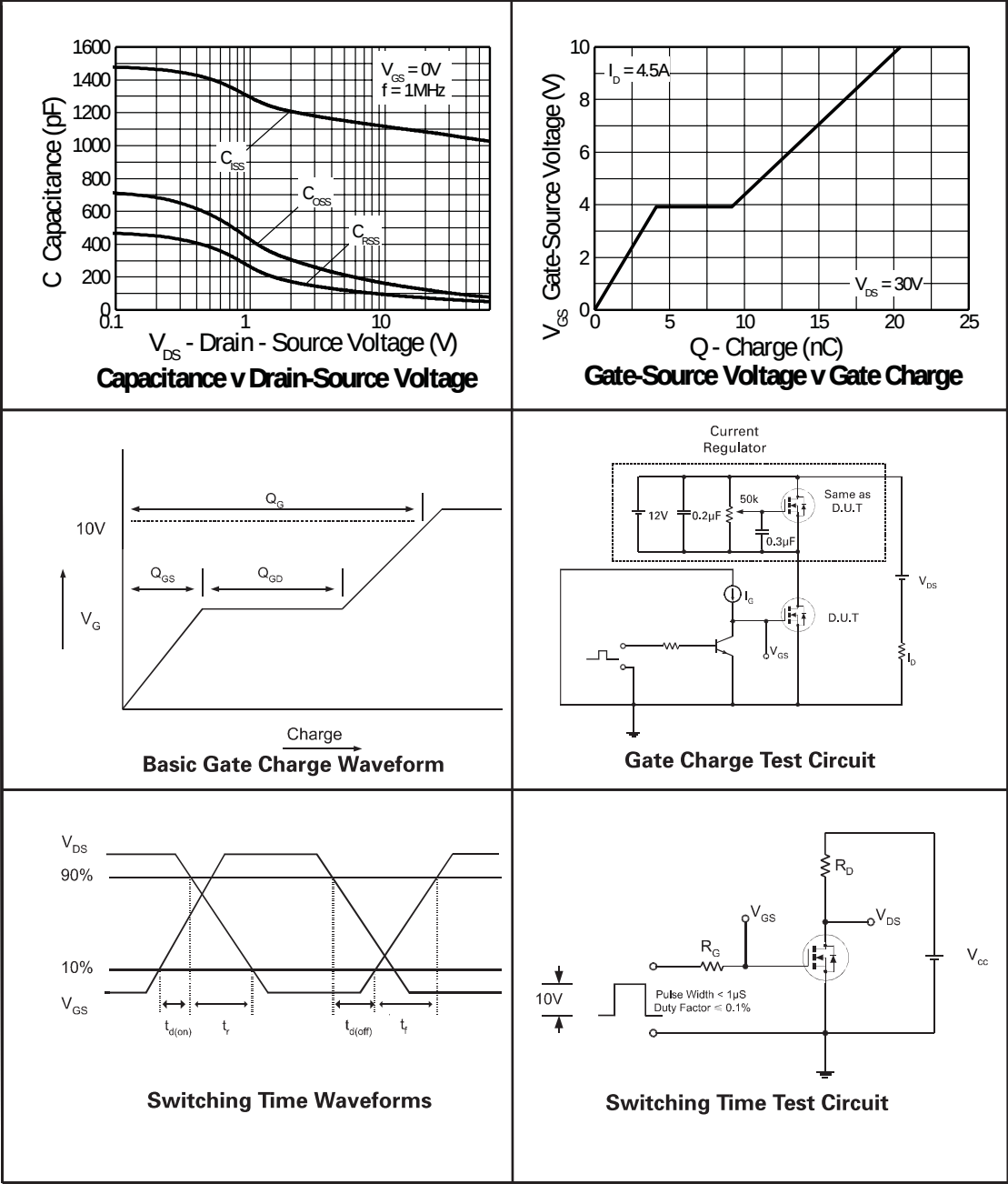
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N-CHANNEL TYPICAL CHARACTERISTICS



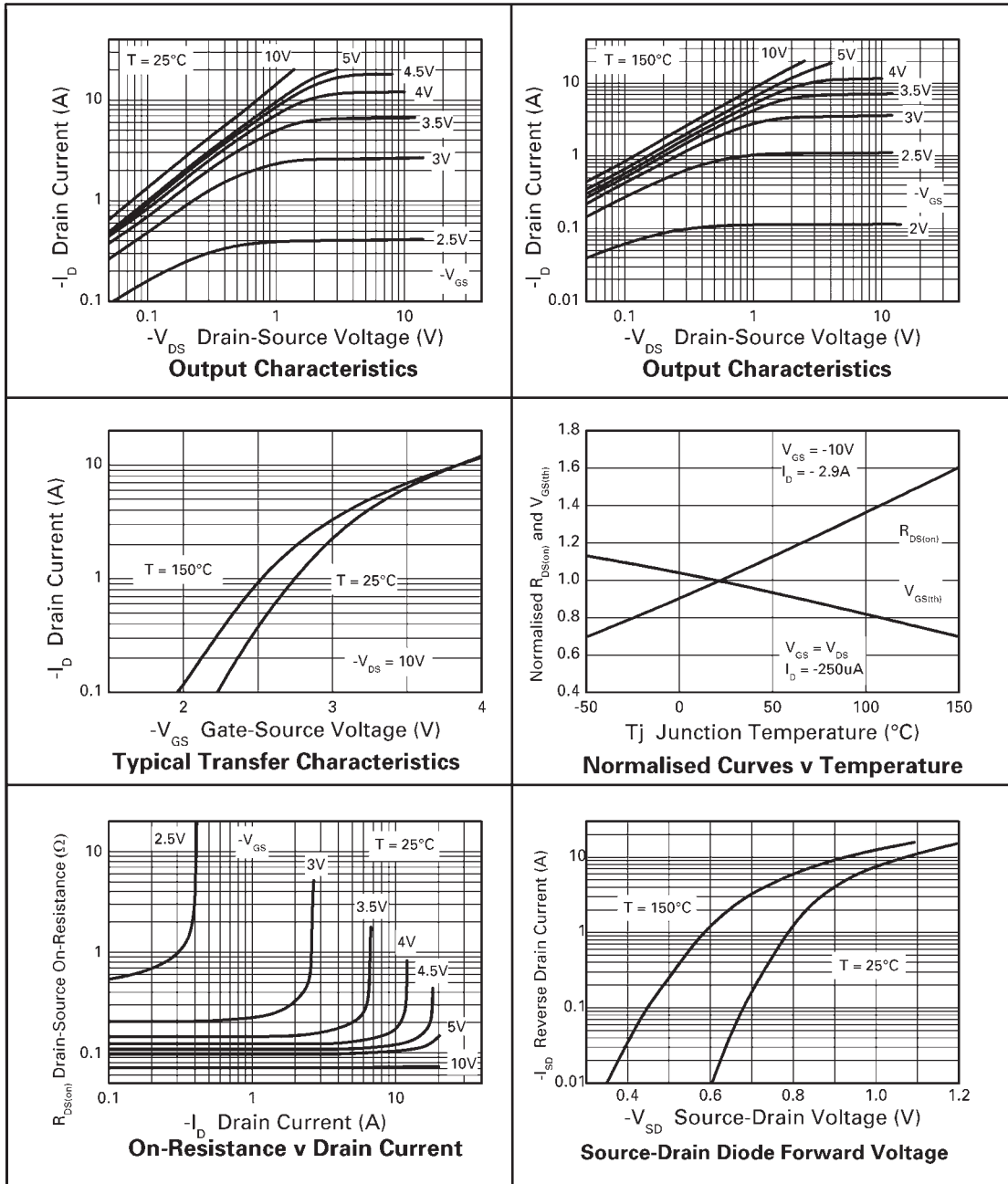
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N-CHANNEL TYPICAL CHARACTERISTICS



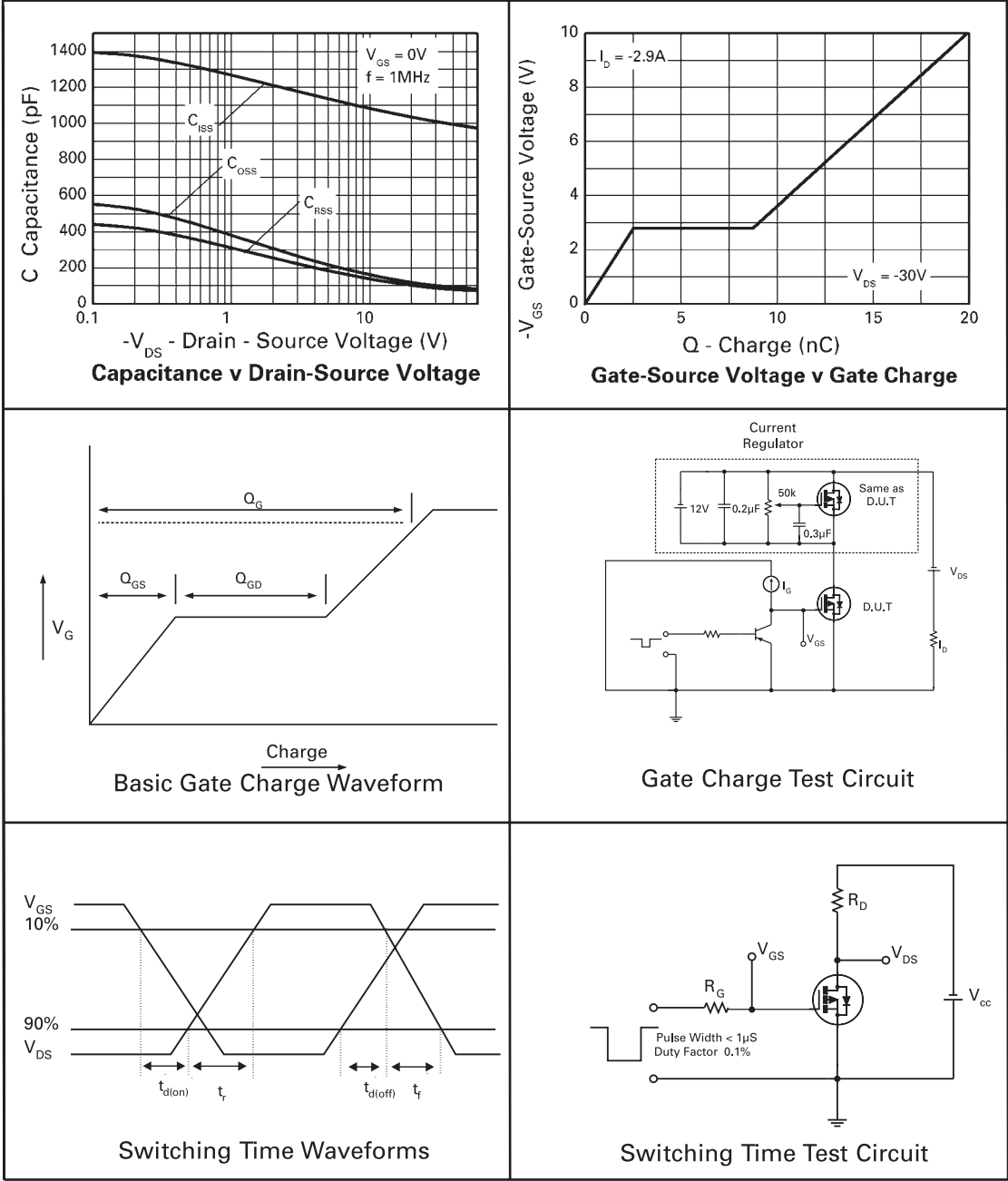
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P-CHANNEL TYPICAL CHARACTERISTICS



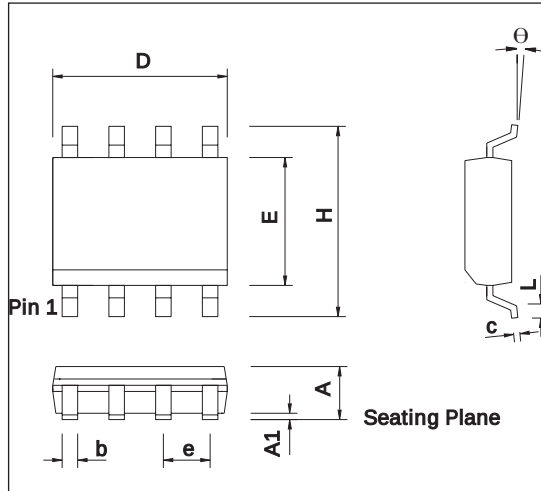
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P-CHANNEL TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES
APPROX IN MILLIMETRES

PACKAGE DIMENSIONS

DIM	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
A	0.053	0.069	1.35	1.75
A1	0.004	0.010	0.10	0.25
D	0.189	0.197	4.80	5.00
H	0.228	0.244	5.80	6.20
E	0.150	0.157	3.80	4.00
L	0.016	0.050	0.40	1.27
e	0.050 BSC		1.27 BSC	
b	0.013	0.020	0.33	0.51
c	0.008	0.010	0.19	0.25
Θ	0°	8°	0°	8°
h	0.010	0.020	0.25	0.50

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